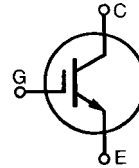


HiPerFAST™ IGBT Lightspeed™ Series

IXGH 40N60C
IXGT 40N60C

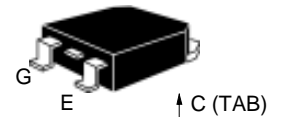
$V_{CES} = 600\text{ V}$
 $I_{C25} = 75\text{ A}$
 $V_{CE(sat)} = 2.5\text{ V}$
 $t_{fi\text{ typ}} = 75\text{ ns}$

Preliminary Data

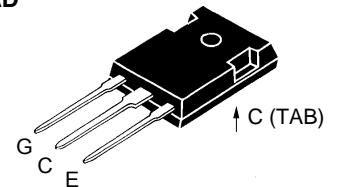


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1\text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	75	A
I_{C110}	$T_C = 110^\circ\text{C}$	40	A
I_{CM}	$T_C = 25^\circ\text{C}, 1\text{ ms}$	150	A
SSOA (RBSOA)	$V_{GE} = 15\text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 10\ \Omega$ Clamped inductive load	$I_{CM} = 80$ @ $0.8 V_{CES}$	A
P_c	$T_C = 25^\circ\text{C}$	250	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque (M3)	1.13/10 Nm/lb.in.	
Weight		TO-247 AD	6 g
		TO-268 SMD	4 g

TO-268
(IXGT)



TO-247 AD
(IXGH)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard packages JEDEC TO-247 and surface mountable TO-268
- High current handling capability
- Latest generation HDMOS™ process
- MOS Gate turn-on - drive simplicity

Applications

- PFC circuits
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

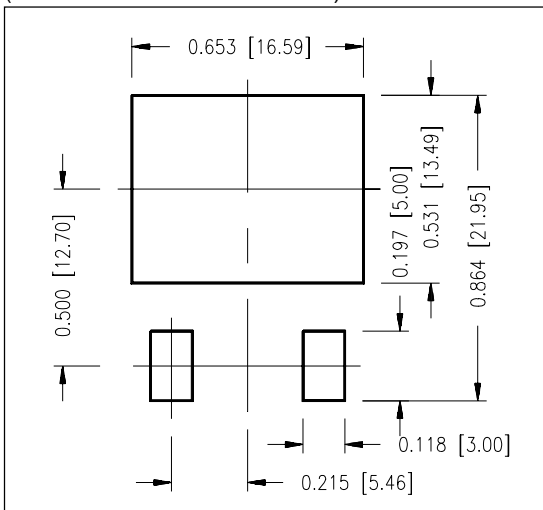
Advantages

- High power density
- Very fast switching speeds for high frequency applications

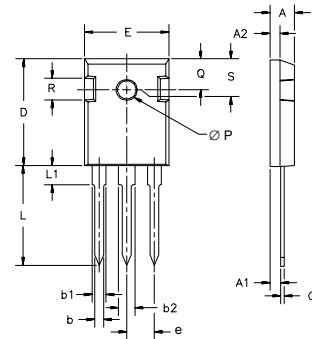
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250\ \mu\text{A}, V_{GE} = 0\text{ V}$	600		V
$V_{GE(th)}$	$I_C = 250\ \mu\text{A}, V_{CE} = V_{GE}$	2.5		V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0\text{ V}$			$T_J = 25^\circ\text{C}$ $T_J = 150^\circ\text{C}$ 200 μA 1 mA
I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C110}, V_{GE} = 15\text{ V}$	2.1	2.5	V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
g_{fs}	$I_C = I_{C110}$; $V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$	30	40	S	
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		3300	pF	
C_{oes}			310	pF	
C_{res}			65	pF	
Q_g	$I_C = I_{C110}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		116	nC	
Q_{ge}			23	nC	
Q_{gc}			55	nC	
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C110}$, $V_{GE} = 15\text{ V}$ $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 4.7\ \Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G		25	ns	
t_{ri}			30	ns	
$t_{d(off)}$			100	150	ns
t_{fi}			75	150	ns
E_{off}			0.85	1.7	mJ
$t_{d(on)}$		Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C110}$, $V_{GE} = 15\text{ V}$ $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 4.7\ \Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G		25	ns
t_{ri}			35	ns	
E_{on}			0.40	mJ	
$t_{d(off)}$			50	ns	
t_{fi}			105	ns	
E_{off}			1.2	mJ	
R_{thJC}				0.50 K/W	
R_{thCK}	(IXGH40N60C)	0.25		K/W	

Min. Recommended Footprint (Dimensions in inches and mm)

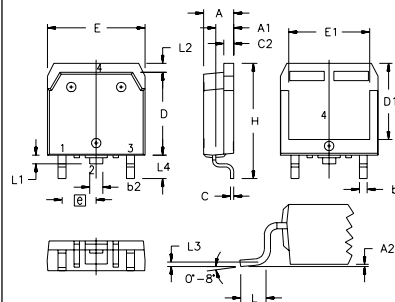


TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

TO-268 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A ₁	.106	.114	2.70	2.90
A ₂	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b ₂	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C ₂	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D ₁	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E ₁	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L ₁	.047	.055	1.20	1.40
L ₂	.039	.045	1.00	1.15
L ₃	.010 BSC		0.25 BSC	
L ₄	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025